

1996 GaAs REL WORKSHOP PROGRAM
November 3, 1996, Peabody Hotel, Orlando, Florida

SESSION I - HBT RELIABILITY K. J. Russell, Chair

Physics-Based Model for Excess Leakage Current in GaAs/AlGaAs HBTs After Bias Stress;
Tim Henderson, Texas Instruments Corporate R&D.

Gradual Degradation of HBTs under Electrical Breakdown Stresses;
I. Khalouf, H. C. Chung, C. J. Uki, and J. C. Wei, and J. C. M. Hwang, Lehigh University.

Degradation Modes of GaAs Heterojunction Bipolar Transistors and Circuits Fabricated in a GaInP Emitter Technology; C. Beaulieu, B. Beggs, J. Bennett, J.P.D. Cook, L. Hobbs, T. Lester, B. Oliver, and R. J. Surridge, Nortel Technology.

SESSION II - HOT ELECTRON & LIGHT EMISSION EFFECTS E. B. Hakim, Chair

Hot Electron Effect on UTET Devices: How to Assess Reliability of High Power Amplifiers;
J. Muraro, F. Coppel and G. Gregoris, Alcatel Espace.

DC and RF Instability of GaAs-based PHEMTs Due to Hot Electrons;
R. Menozzi, M. Borgarino, P. Cova, Y. Baeyens, M. Pavesi, and F. Fantini, University of Parma.

An Anomalous Overshoot of Drain Currents Due to Hot Electrons in GaAs MESFETs Driven by Gate Pulse; N. Andoh, H. Matsubayashi, K. Hosogi, T. Sonoda, and M. Otsubo, Mitsubishi Electric Corp.

Electroluminescence: An Essential Technique for Characterization of HBTs Before & After Bias Stress;
Tim Henderson, Texas Instruments Corporate R&D.

Light Emission as an Analysis Tool for GaAs ICs; Bill Roesch, TriQuint Semiconductor.

SESSION M - HYDROGEN EFFECTS S.A. Kayali, Chair

GaAs PHEMT Hydrogen Sensitivity Study; Ken Decker, Texas Instruments.

Modeling of Hydrogen Effects in GaAs FETS; D. Roncour and S. Kayali, JPL.

SESSION IV - LIFETESTING, DISCUSSION W. J. Roesch, Chair

Reliability Life Testing and Failure Analysis of GaAs NMC Ku-Band Driver Amplifiers;
J. Mittereder, J. Roussos, K. Christianson, and W. T. Anderson, Naval Research Laboratory.

Problems with Predicting Device Life in Space Applications; K. Russell, Aerospace Corporation.

Short Duration in Situ Life Test: A New Method for GaAs Transistor Evaluation;
F. Coppel & G. Gregoris, Alcatel Espace.